**Product data sheet** 

# 1. General description

PNP low V<sub>CEsat</sub> transistor in a SOT223 plastic package.

NPN complement: PBSS4540Z-Q

## 2. Features and benefits

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

# 3. Applications

- Supply line switching circuits
- · Battery management applications
- DC/DC converter applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers)
- MOSFET driver applications.

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-40	V
I <sub>C</sub>	collector current		-	-	-5	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-10	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	55	80	mΩ

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	С
2	С	collector		
3	Е	emitter		B—(m)
4	С	collector	<b>□</b> 1 <b>□</b> 2 <b>□</b> 3	É
			SC-73 (SOT223)	sym132



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# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PBSS5540Z-Q		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223		

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS5540Z-Q	PB5540

# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-5	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-10	Α
I <sub>BM</sub>	peak base current			-	-2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	1.35	W
			[2]	-	2	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

## 9. Thermal characteristics

### **Table 6. Thermal characteristics**

	Symbol	Parameter	Conditions		Min	Тур	Max	Unit
	R <sub>th(j-a)</sub> thermal resistance from junction to ambient	in free air	[1]	-	-	92	K/W	
			[2]	-	-	62	K/W	

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

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# 10. Characteristics

### **Table 7. Characteristics**

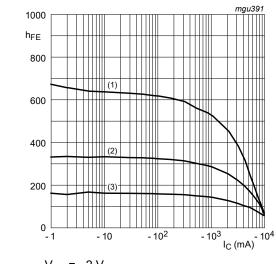
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	I <sub>C</sub> = -100 μA; I <sub>E</sub> = 0 A	-40	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C$ = -10 mA; $I_B$ = 0 A; $T_{amb}$ = 25 °C	-40	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	$I_E = -100 \mu A; I_B = 0 mA; T_{amb} = 25 °C$	-6	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -500 mA; T <sub>amb</sub> = 25 °C	250	350	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	300	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	150	250	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	50	150	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = -500 mA; I <sub>B</sub> = -5 mA; T <sub>amb</sub> = 25 °C	-	-80	-120	mV
	saturation voltage	I <sub>C</sub> = -1 A; I <sub>B</sub> = -10 mA; T <sub>amb</sub> = 25 °C	-	-120	-170	mV
		I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; T <sub>amb</sub> = 25 °C	-	-110	-160	mV
		I <sub>C</sub> = -5 A; I <sub>B</sub> = -500 mA; T <sub>amb</sub> = 25 °C	-	-250	-375	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	55	80	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = -5 A; I <sub>B</sub> = -500 mA; T <sub>amb</sub> = 25 °C	-	-	-1.3	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -2 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-0.8	-1.25	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	60	120	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	90	105	pF

3 / 10

- 1.2

 $V_{\text{BE}}$ (V)

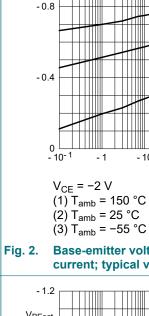
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(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 1. DC current gain as a function of collector current; typical values



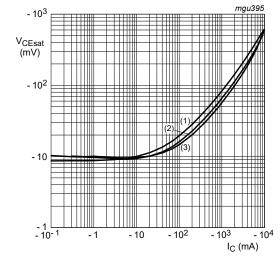
Base-emitter voltage as a function of collector current; typical values

- 10

- 10<sup>2</sup>

- 10<sup>3</sup>

- 10<sup>4</sup> I<sub>C</sub> (mA)



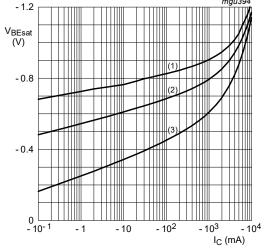
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

$$(2) T_{amb} = 25 °C$$

$$(3) T_{amb} = -55 °C$$

Fig. 3. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

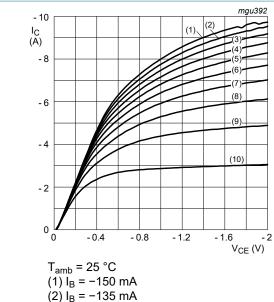
$$(1) T_{amb} = 150 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

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 $(3) I_B^- = -120 \text{ mA}$ 

 $(4) I_B = -105 \text{ mA}$ 

 $(5) I_B = -90 \text{ mA}$ 

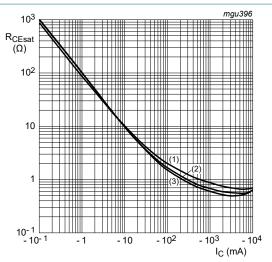
(6)  $I_B = -75 \text{ mA}$ 

 $(7) I_B = -60 \text{ mA}$ 

 $(8) I_B = -45 \text{ mA}$ (9)  $I_B = -30 \text{ mA}$ 

 $(10) I_B = -15 \text{ mA}$ 

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 20$ 

(1)  $T_{amb} = 150 \, ^{\circ}C$ (2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 6. Collector-emitter equivalent on-resistance as a function of collector current; typical values

## 11. Test information

### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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# 12. Package outline

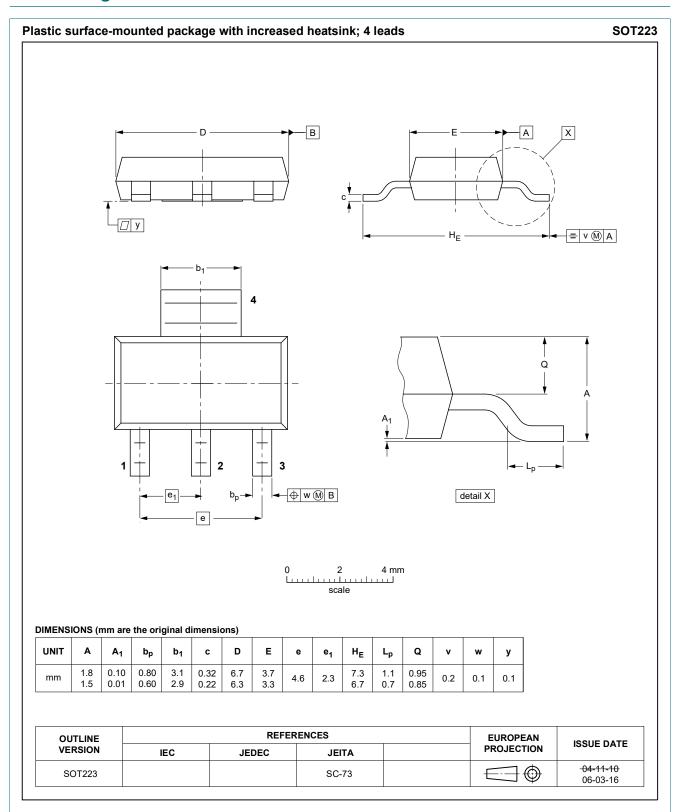
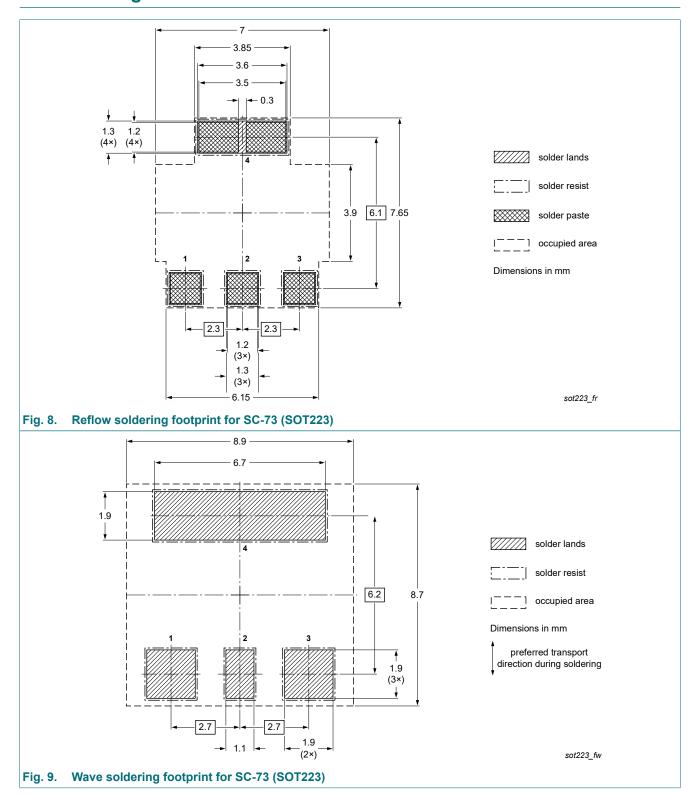


Fig. 7. Package outline SC-73 (SOT223)

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# 13. Soldering



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# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5540Z-Q v.1	20211130	Product data sheet	-	-

#### 40 V low VCEsat PNP transistor

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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# PBSS5540Z-Q

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